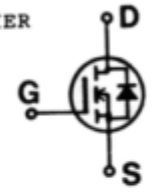
2SK351

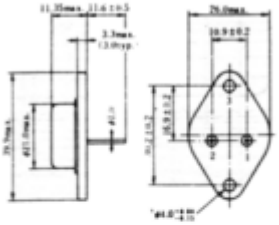
SILICON N-CHANNEL MOS FET

HIGH SPEED POWER SWITCHING
HIGH FREQUENCY POWER AMPLIFIER



Features;

- High Breakdown Voltage.
- High Speed Switching.
- High Cutoff Frequency.
- No Secondary Breakdown.
- Suitable for Switching Regulator, DC-DC Converter, RF Amplifiers, and Ultrasonic Power Oscillators.



1. Gate
2. Source
3. Drain (Case)

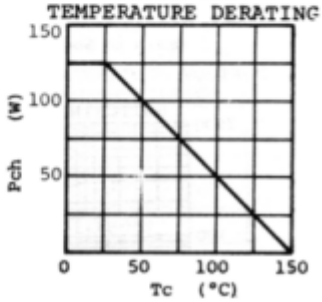
(JEDEC TO-3)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	800	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current	I_D	5	A
Drain Peak Current	$I_{D(peak)}$	10	A
Body-Drain Diode Reverse Drain Current	I_{DR}	5	A
Channel Dissipation	Pch*	125	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 ~ +150	°C

*Value at Tc=25°C

POWER VS. TEMPERATURE DERATING



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=10mA, V_{GS}=0	800	-	-	V
Gate-Source Leak Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0	-	-	±1	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=640V, V_{GS}=0	-	-	1	mA
Gate-Source Cutoff Voltage	$V_{GS(off)}$	I_D=1mA, V_{DS}=10V	1.0	-	5.0	V
Static Drain-Source On State Resistance	$R_{DS(on)}$	I_D=3A, V_{GS}=15V *	-	1.7	3.0	Ω
Drain-Source Saturation Voltage	$V_{DS(on)}$	I_D=3A, V_{GS}=15V *	-	5.0	9.0	V
Forward Transfer Admittance	$\|yfs\|$	I_D=3A, V_{DS}=10V *	1.0	2.0	-	S
Input Capacitance	Ciss	V_{DS}=10 V, V_{GS}=0 f=1MHz	-	1900	-	pF
Output Capacitance	Coss		-	320	-	pF
Reverse Transfer Capacitance	Crss		-	40	-	pF
Turn-On Delay Time	$t_{d(on)}$	I_D=2A, V_{GS}=15V R_L=15Ω	-	30	-	ns
Rise Time	t_r		-	70	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	220	-	ns
Fall Time	t_f		-	80	-	ns
Body-Drain Diode Forward Voltage	V_{DF}	I_F=3A, V_{GS}=0	-	0.8	-	V
Body-Drain Diode Reverse Recovery Time	t_{rr}	I_F=3A, V_{GS}=0	-	2.2	-	μs

*Pulse Test

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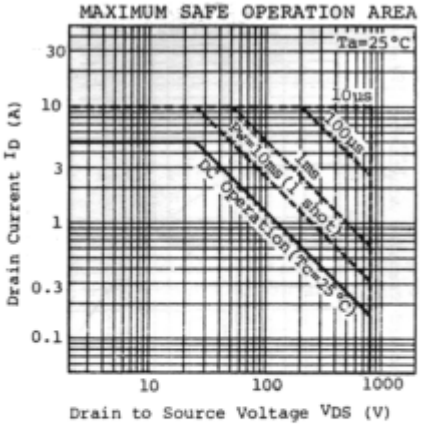
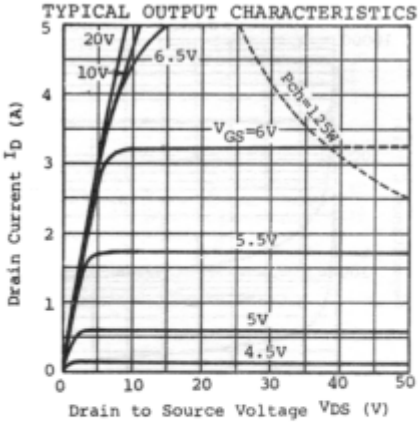
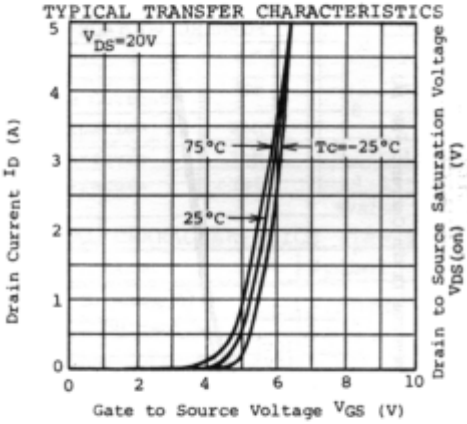
MAXIMUM SAFE OPERATION AREA



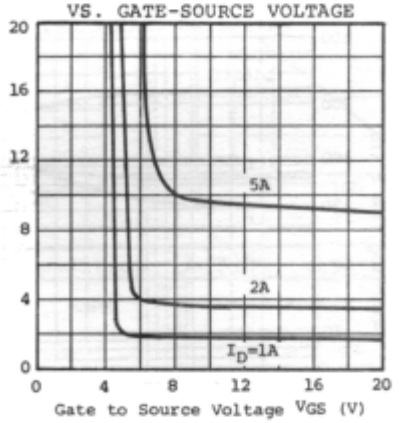
TYPICAL OUTPUT CHARACTERISTICS



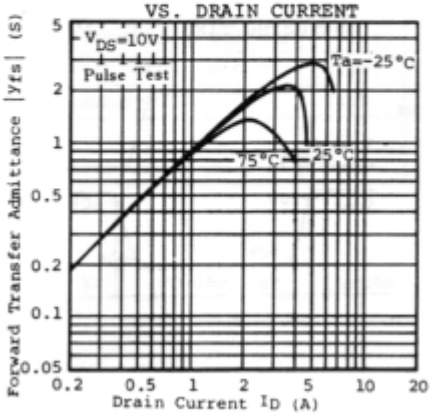
TYPICAL TRANSFER CHARACTERISTICS



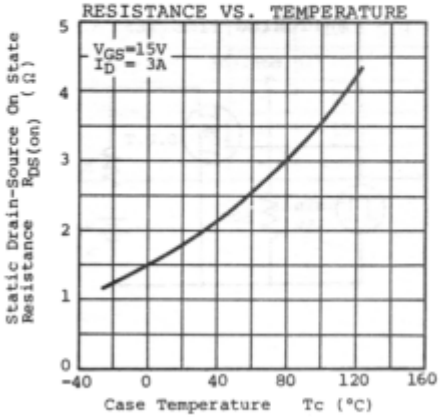
DRAIN-SOURCE SATURATION VOLTAGE VS. GATE-SOURCE VOLTAGE



FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT



STATIC DRAIN-SOURCE ON STATE RESISTANCE VS. TEMPERATURE



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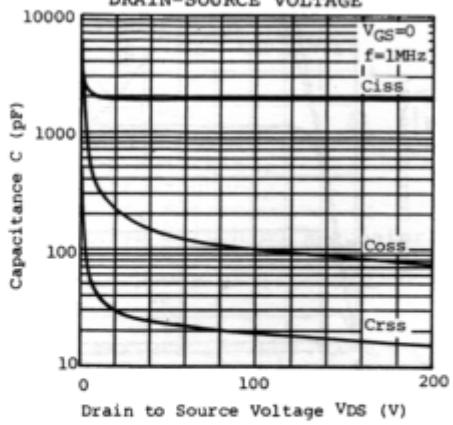
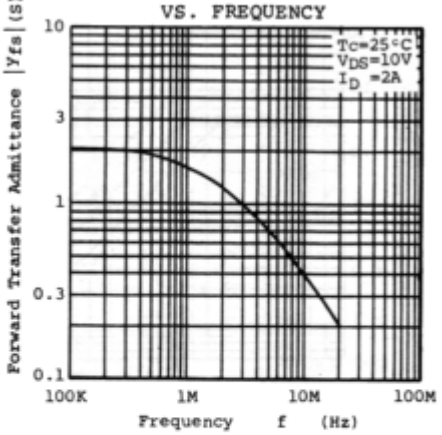
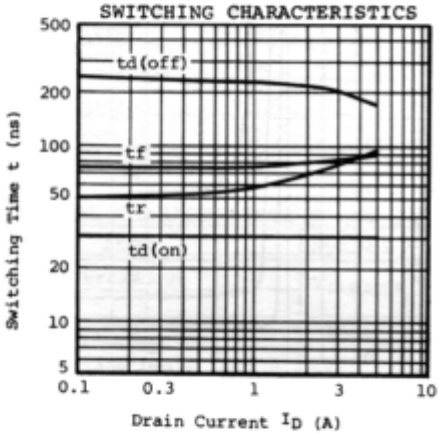
TYPICAL CAPACITANCE VS. DRAIN-SOURCE VOLTAGE



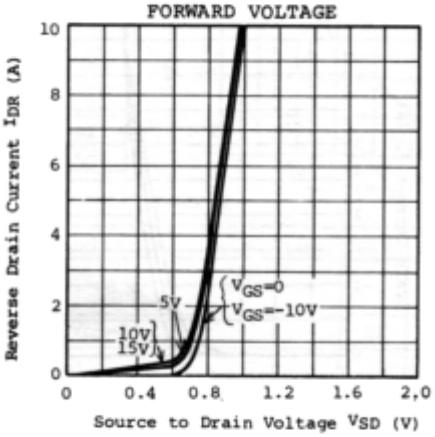
FORWARD TRANSFER ADMITTANCE VS. FREQUENCY



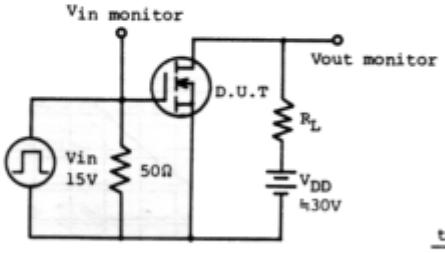
SWITCHING CHARACTERISTICS



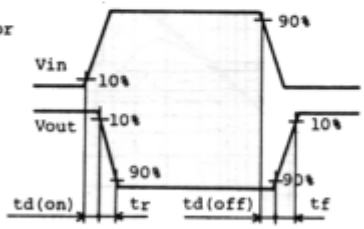
MAXIMUM BODY-DRAIN DIODE FORWARD VOLTAGE



SWITCHING TIME TEST CIRCUIT



SWITCHING TIME TEST WAVEFORMS



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